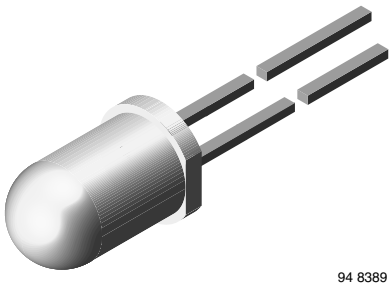
Infrared Emitting Diode, 875 nm, GaAlAs



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FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): Ø 5
- Peak wavelength: λ_p = 875 nm
- High reliability
- Angle of half intensity: φ = ± 24°
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

RoHS COMPLIANT
HALOGEN FREE

DESCRIPTION

The TSHA650. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

APPLICATIONS

- Infrared remote control and free air data transmission systems with comfortable radiation angle
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorbtion of 875 nm radiation in glass

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSHA6500	20	± 24	875	600
TSHA6501	25	± 24	875	600
TSHA6502	30	± 24	875	600
TSHA6503	35	± 24	875	600

Note
Test conditions see table “Basic Characteristics”

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA6500	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾
TSHA6501	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾
TSHA6502	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾
TSHA6503	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾

Note
MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	2.5	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note
T_{amb} = 25 °C, unless otherwise specified

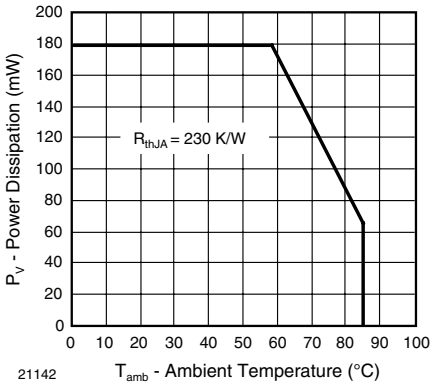

Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

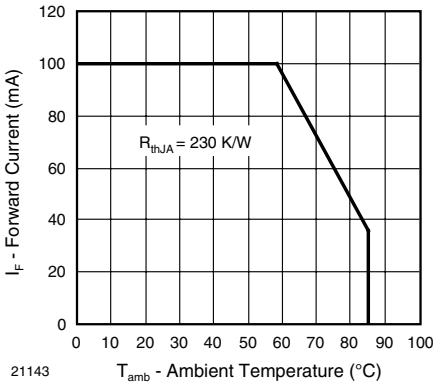

Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.5	1.8	V
Temperature coefficient of V_F	I_F = 100 mA	TK_{VF}		- 1.6		mV/K
Reverse current	V_R = 5 V	I_R			100	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		20		pF
Temperature coefficient of ϕ_e	I_F = 20 mA	$TK\phi_e$		- 0.7		%/K
Angle of half intensity		φ		± 24		deg
Peak wavelength	I_F = 100 mA	λ_p		875		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		80		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.2		nm/K
Rise time	I_F = 100 mA	t_r		600		ns
	I_F = 1 A	t_r		300		ns
Fall time	I_F = 100 mA	t_f		600		ns
	I_F = 1 A	t_f		300		ns
Virtual source diameter		d		2.2		mm

Note

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TYPE DEDICATED CHARACTERISTICS							
PARAMETER	**TEST CONDITION**	**PART**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Forward voltage	I_F = 1 A, t_p = 100 µs	TSHA6500	V_F		2.8	3.5	V
		TSHA6501	V_F		2.8	3.5	V
		TSHA6502	V_F		2.8	3.5	V
		TSHA6503	V_F		2.8	3.5	V
Radiant intensity	I_F = 100 mA, t_p = 20 ms	TSHA6500	I_e	12	20	60	mW/sr
		TSHA6501	I_e	16	25	60	mW/sr
		TSHA6502	I_e	20	30	60	mW/sr
		TSHA6503	I_e	24	35	60	mW/sr
	I_F = 1 A, t_p = 100 µs	TSHA6500	I_e	100	160		mW/sr
		TSHA6501	I_e	130	200		mW/sr
		TSHA6502	I_e	160	240		mW/sr
		TSHA6503	I_e	200	280		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	TSHA6500	ϕ_e		22		mW
		TSHA6501	ϕ_e		23		mW
		TSHA6502	ϕ_e		24		mW
		TSHA6503	ϕ_e		25		mW

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

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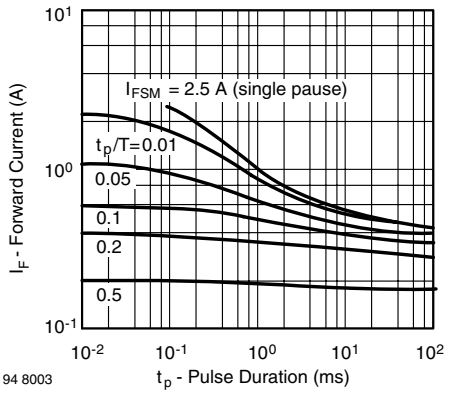


Fig. 3 - Pulse Forward Current vs. Pulse Duration

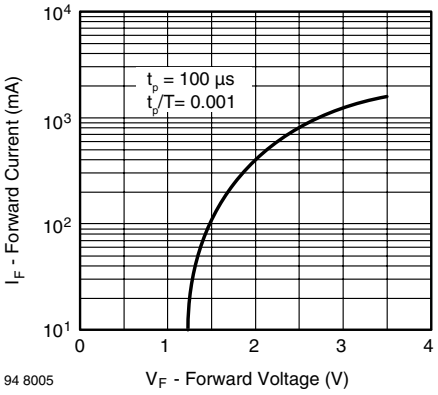


Fig. 4 - Forward Current vs. Forward Voltage

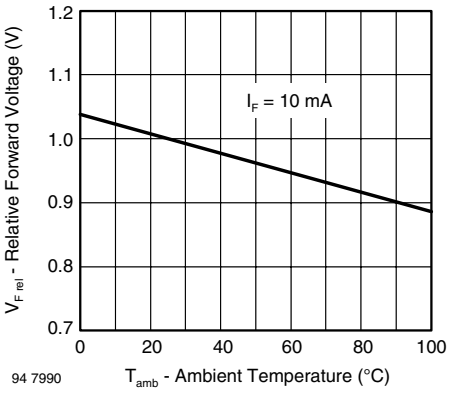


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

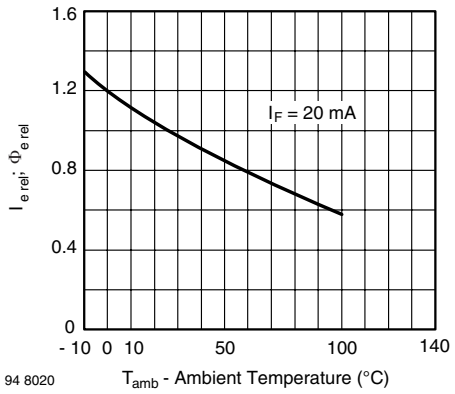


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

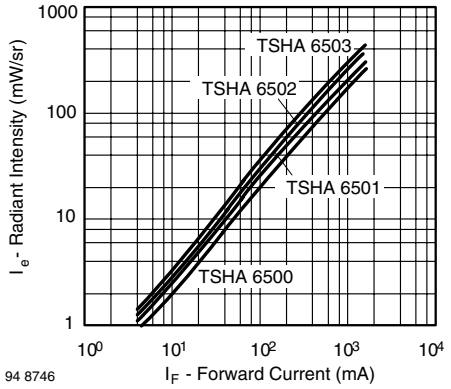


Fig. 6 - Radiant Intensity vs. Forward Current

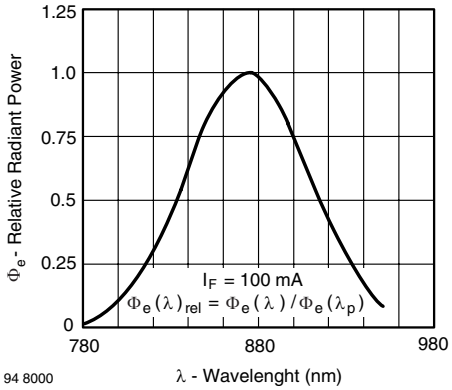


Fig. 9 - Relative Radiant Power vs. Wavelength

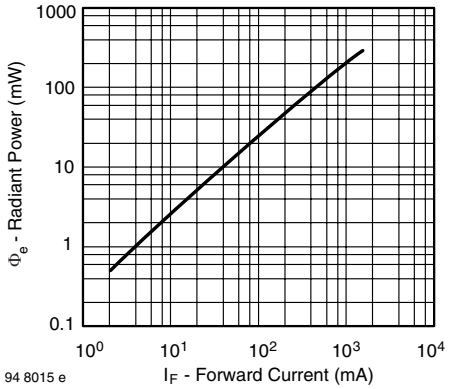


Fig. 7 - Radiant Power vs. Forward Current

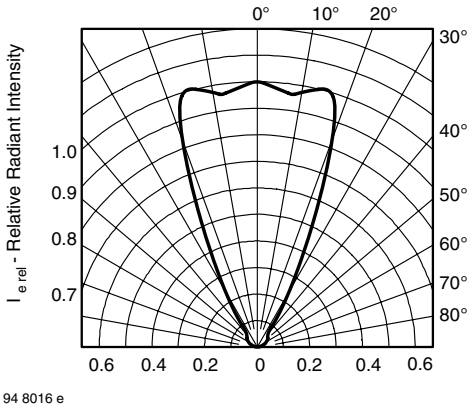
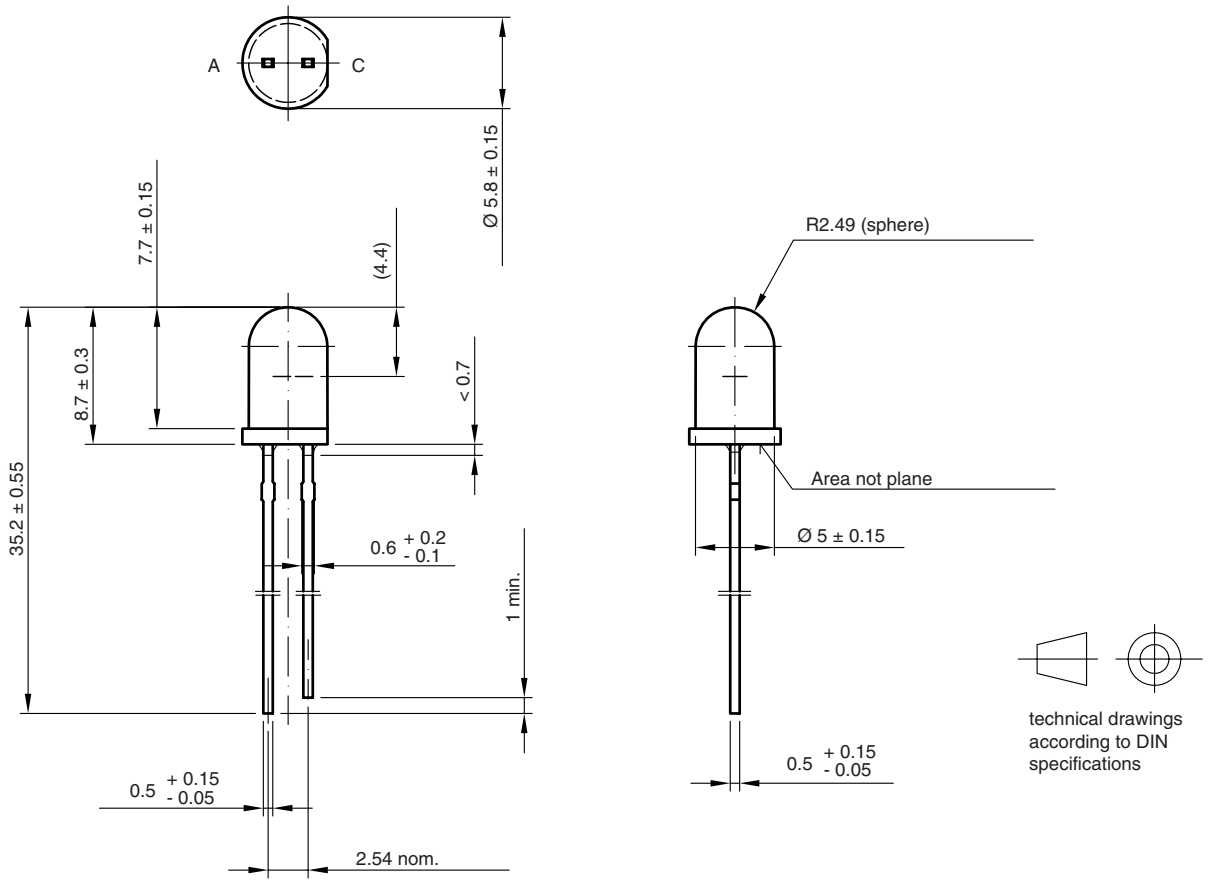


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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